# NSN 5961-01-624-7504

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## **Overall Length:**

Between 1.335 inches and 1.345 inches

## **Overall Height:**

Between 0.125 inches and 0.170 inches

# **Overall Width:**

Between 0.380 inches and 0.390 inches

#### **Function For Which Designed:**

Programmable transistor

#### **Internal Configuration:**

Field effect

## Electrode Internally-electrically Connected To Case:

Gate

**Features Provided:** 

Gold plated leads

Voltage Rating In Volts Per Characteristic:

65.0 drain to source voltage

**Current Rating Per Characteristic:** 

10.0 microamperes zero-gate-voltage drain current

## **Power Rating Per Characteristic:**

298.0 watts total device dissipation

## Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Product Name:

Rf power field effect transistor

## **Special Features:**

In tape and reel, r3 suffix= 250 units per 56mm, 13 inch reel; rohs compliant; designed for gsm and gsm edge base station applications with frequencies from 921 to 960 mhz; designed for maximum gain and instertion phase flatness; high gain and broadband performance of these devices make them ideal for large signal, common source amplifier applications in 28 volt base stations; high efficiency; high linearity; integrated esd protection

Terminal Type And Quantity:

3 pin

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0